







\*D1001

\*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET

\*May 2004

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*          _____GATE
*          I      _____DRAIN
*          I      I      _____SOURCE
*          I      I      I
.SUBCKT D1001  10  20  30
*Cin1,Cin2 & Lin model the input side of the package
Cin1  10   30   0.31p
Lin   10   11   0.64n
Cin2  11   30   0.24p
LG    11   12   1n      ;Gate bond wire inductance
CGS   12   13   46p     ;Gate-source capacitance
MOS   14   12   13      13  D1001 L=0.9U W=0.056      ;D G S B LEVEL1
JFET  16   13   14      D1001                        ;D G S
DBODY 13   16           D1001                        ;P N
LS    13   30   1n      ;Source bond wire inductance
CGD   12   16   1p      ;Gate-drain feedback capacitance

*Cout1,Cout2 & Lout model the output side of the package
Cout1 16   30   0.65p
Lout   16   20   1.5n
Cout2 20   30   0.6p

.MODEL D1001 NMOS (VTO=4.76 KP=2.811E-5 LAMBDA=0.032 RD=0.076 RS=0.306)
.MODEL D1001 NJF (VTO=-4.3 BETA=0.25 LAMBDA=0.54)
.MODEL D1001 D (CJO=82.2P RS=0.25 VJ=0.7 M=0.35 BV=75)

.ENDS
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